

NDF04N60Z, NDP04N60Z, NDD04N60Z



ON Semiconductor®

<http://onsemi.com>

N-Channel Power MOSFET 1.8 Ω, 600 Volts

Features

- Low ON Resistance
- Low Gate Charge
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Adapter (Notebook, Printer, Gaming)
- LCD Panel Power
- Lighting Ballasts

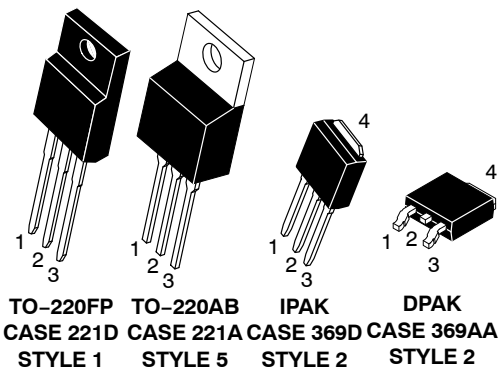
ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	NDF	NDD/NDP	Unit
Drain-to-Source Voltage	V _{DSS}	600 (Note 1)		V
Continuous Drain Current	I _D	4.0 (Note 2)		A
Continuous Drain Current T _A = 100°C	I _D	2.7 (Note 2)		A
Pulsed Drain Current, V _{GS} @ 10V	I _{DM}	14 (Note 2)		A
Power Dissipation (Note 1)	P _D	28	95	W
Gate-to-Source Voltage	V _{GS}	±30		V
Single Pulse Avalanche Energy, L = 6.4 mH, I _D = 4.0 A	E _{AS}	51		mJ
ESD (HBM) (JESD 22-114-B)	V _{esd}	2500		V
RMS Isolation Voltage (t = 0.3 sec., R.H. ≤ 30%, T _A = 25°C) (Figure 13)	V _{ISO}	4500	-	V
Peak Diode Recovery	dv/dt	4.5 (Note 3)		V/ns
Continuous Source Current (Body Diode)	I _S	4.0		A
Maximum Temperature for Soldering Leads, 0.063" (1.6 mm) from Case for 10 s Package Body for 10 s	T _L T _{PKG}	300 260		°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C

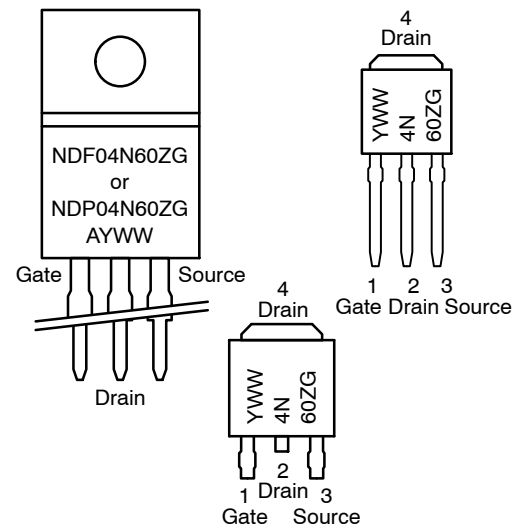
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1" sq. pad size, 1 oz cu
2. Limited by maximum junction temperature
3. I_{SD} = 4.0 A, di/dt ≤ 100 A/μs, V_{DD} ≤ BV_{DSS}, T_J = +150°C

V _{DSS}	R _{DS(ON)} (TYP) @ 2 A
600 V	1.8 Ω



MARKING DIAGRAMS



- A = Location Code
- Y = Year
- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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THERMAL RESISTANCE

Parameter	Symbol	NDF04N60Z	NDD/NDP	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	4.4	1.3	°C/W
Junction-to-Ambient Steady State (Note 4)	$R_{\theta JA}$	50	50	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	BV_{DSS}	600			V
Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1\text{ mA}$	$\Delta BV_{DSS}/\Delta T_J$		0.6		V/°C
Drain-to-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}			1	μA
					50	
Gate-to-Source Forward Leakage	$V_{GS} = \pm 20\text{ V}$	I_{GSS}			± 10	μA

ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.0\text{ A}$	$R_{DS(on)}$		1.8	2.0	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	$V_{GS(th)}$	3.0		4.5	V
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 2.0\text{ A}$	g_{FS}		3.3		S

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	C_{iss}		535		pF
Output Capacitance		C_{oss}		62		
Reverse Transfer Capacitance		C_{rss}		14		
Total Gate Charge	$V_{DD} = 300\text{ V}, I_D = 4.0\text{ A},$ $V_{GS} = 10\text{ V}$	Q_g		19		nC
Gate-to-Source Charge		Q_{gs}		3.9		
Gate-to-Drain ("Miller") Charge		Q_{gd}		10		
Gate Resistance		R_g		4.7		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 4.0\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 5\ \Omega$	$t_{d(on)}$		13		ns
Rise Time		t_r		9.0		
Turn-Off Delay Time		$t_{d(off)}$		24		
Fall Time		t_f		15		

SOURCE-DRAIN DIODE CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Diode Forward Voltage	$I_S = 4.0\text{ A}, V_{GS} = 0\text{ V}$	V_{SD}			1.6	V
Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 30\text{ V}$ $I_S = 4.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	t_{rr}		285		ns
Reverse Recovery Charge		Q_{rr}		1.3		μC

4. Insertion mounted

5. Pulse Width $\leq 380\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

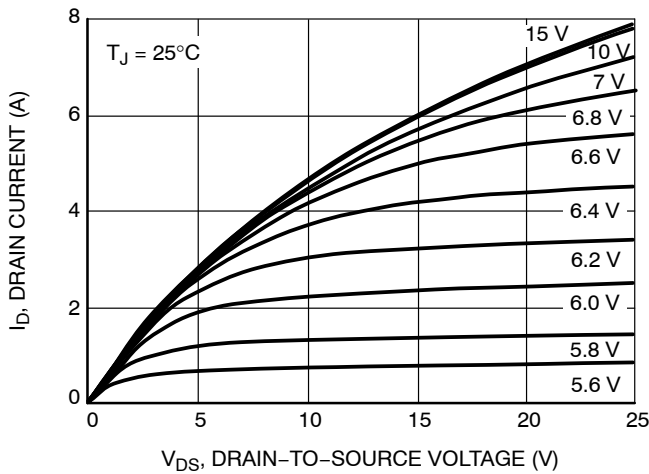


Figure 1. On-Region Characteristics

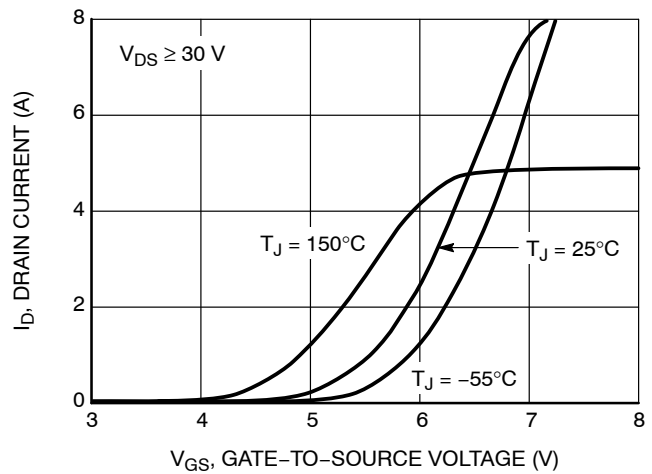


Figure 2. Transfer Characteristics

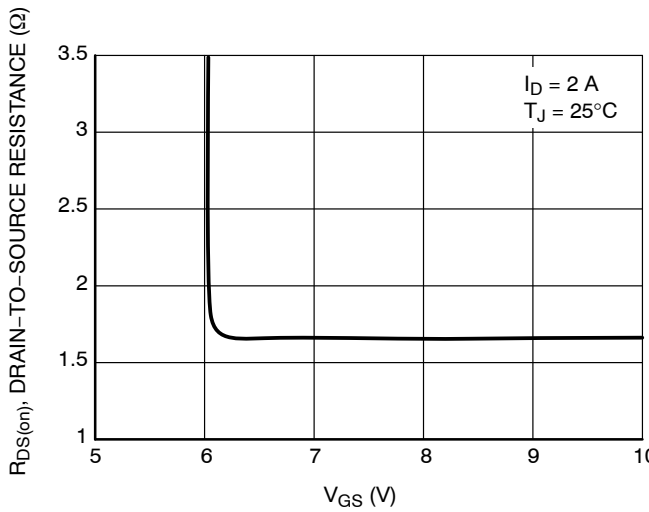


Figure 3. On-Resistance vs. Gate Voltage

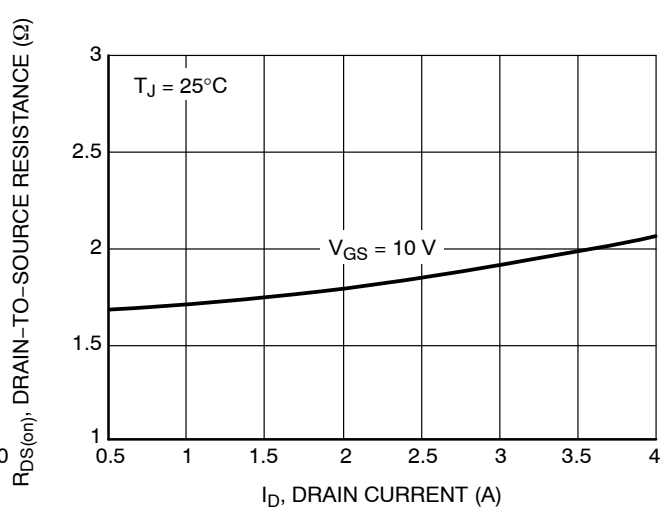


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

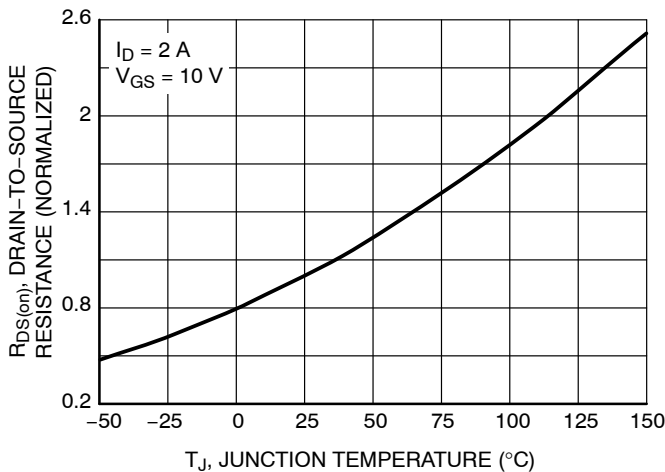


Figure 5. On-Resistance Variation with Temperature

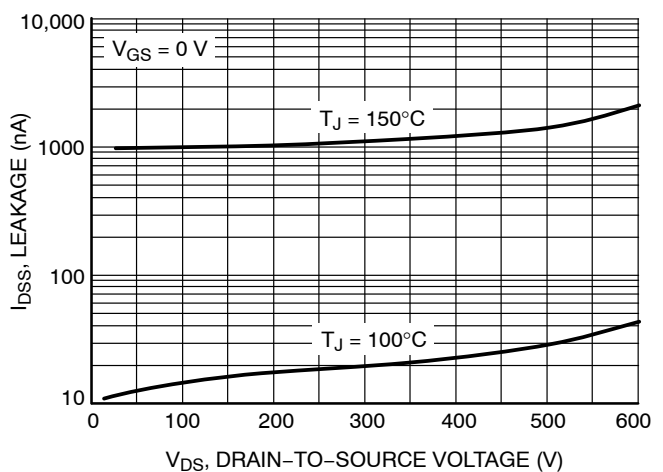


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

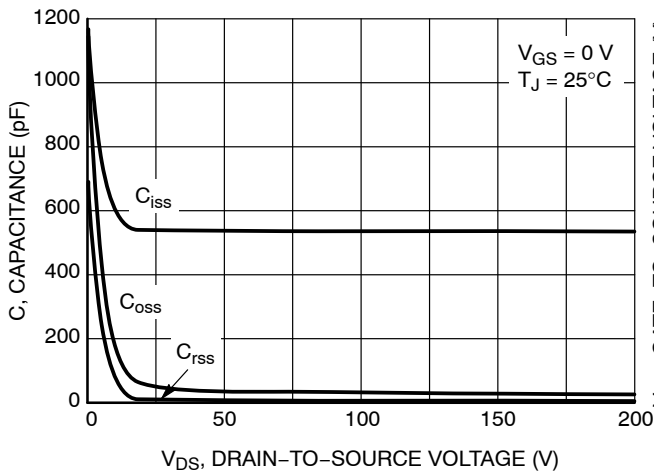


Figure 7. Capacitance Variation

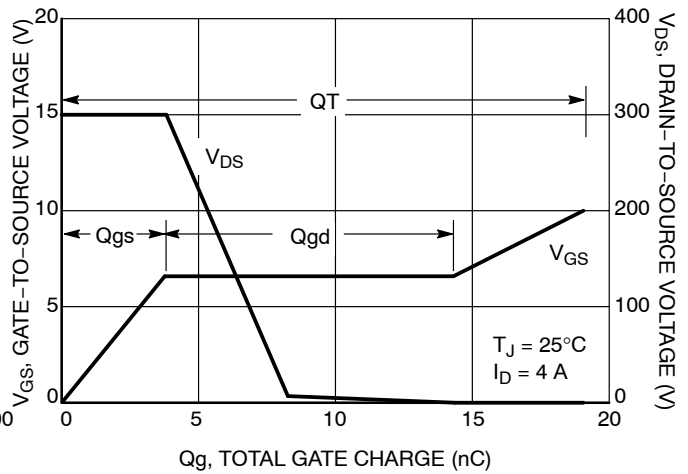


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

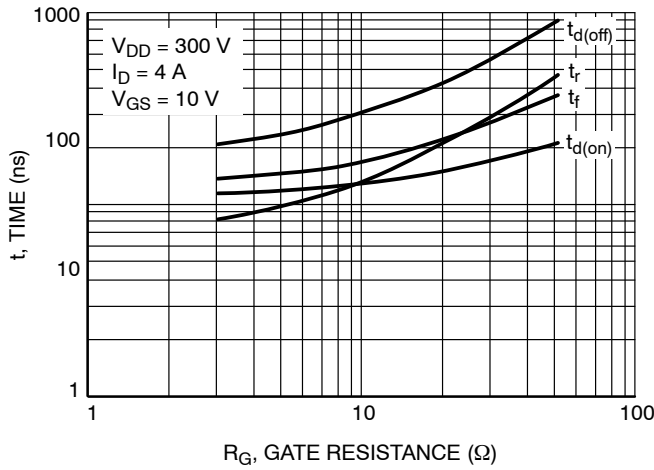


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

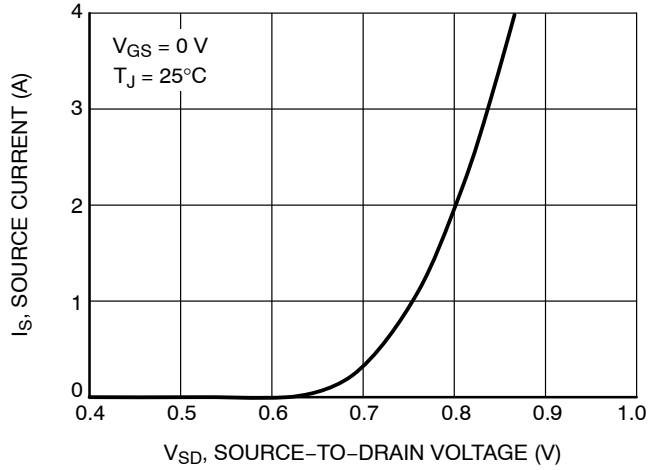


Figure 10. Diode Forward Voltage vs. Current

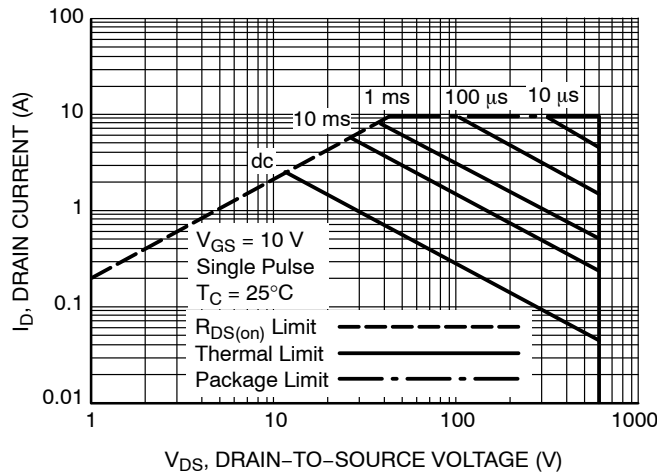


Figure 11. Maximum Rated Forward Biased Safe Operating Area for NDF04N60Z

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TYPICAL CHARACTERISTICS

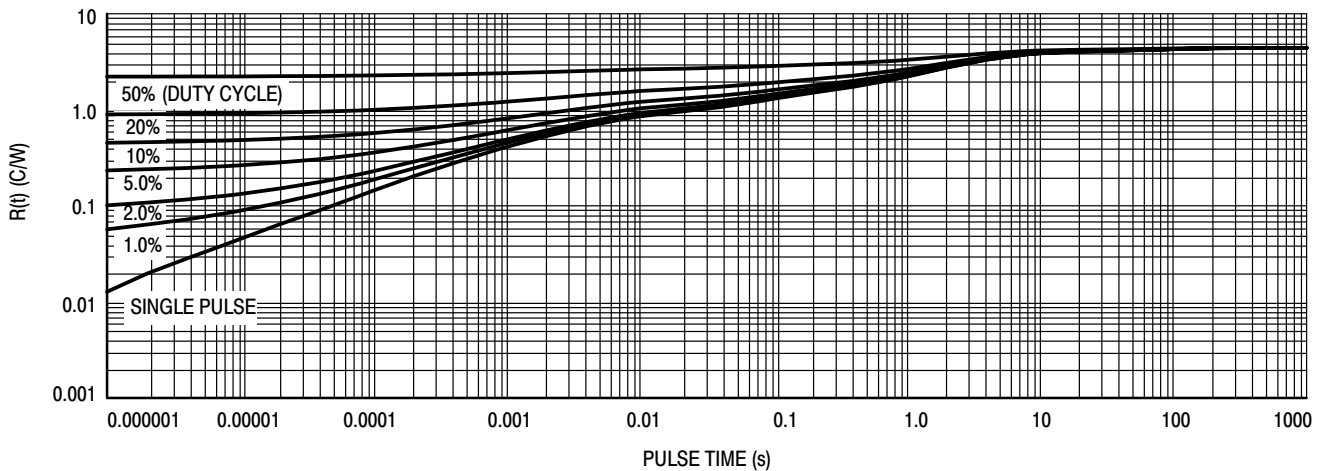


Figure 12. Thermal Impedance for NDF04N60Z

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NDF04N60ZG	TO-220FP (Pb-Free)	50 Units / Rail
NDP04N60ZG	TO-220AB (Pb-Free)	In Development
NDD04N60Z-1G	IPAK (Pb-Free)	In Development
NDD04N60ZG	DPAK (Pb-Free)	In Development

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

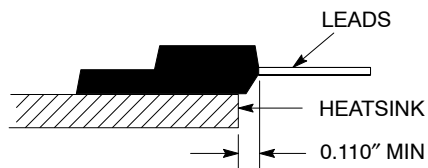


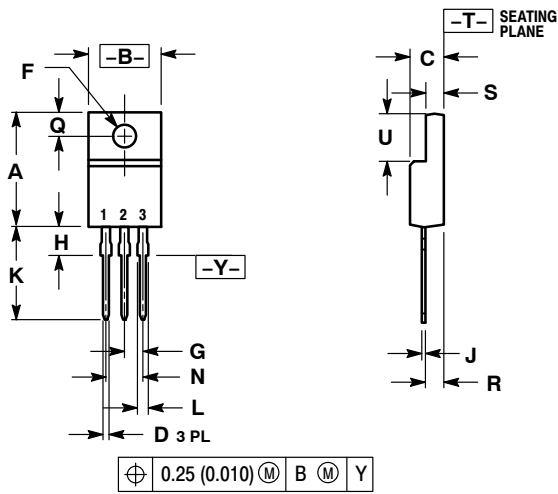
Figure 13. Mounting Position for Isolation Test

Measurement made between leads and heatsink with all leads shorted together.

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PACKAGE DIMENSIONS

TO-220 FULLPAK CASE 221D-03 ISSUE J

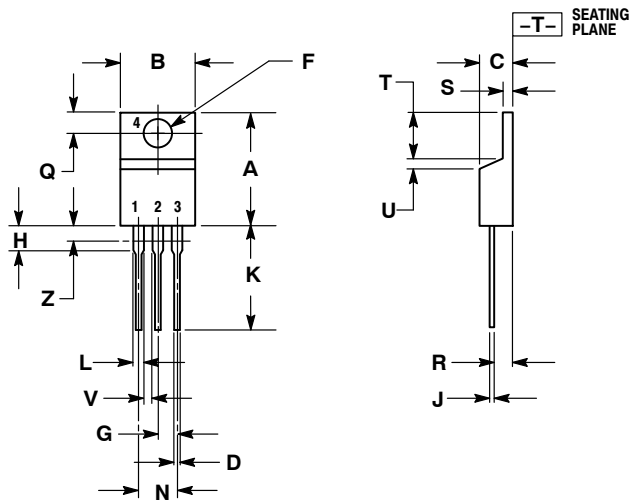


- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - CONTROLLING DIMENSION: INCH
 - 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

- STYLE 1:
- PIN 1. GATE
 - DRAIN
 - SOURCE

TO-220AB CASE 221A-09 ISSUE AE



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - CONTROLLING DIMENSION: INCH.
 - DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

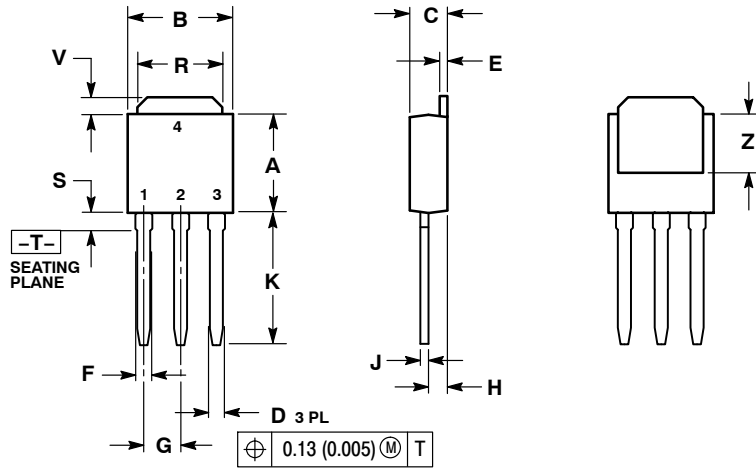
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 5:
- PIN 1. GATE
 - DRAIN
 - SOURCE
 - DRAIN

NDF04N60Z, NDP04N60Z, NDD04N60Z

PACKAGE DIMENSIONS

I_{PAK}
CASE 369D-01
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

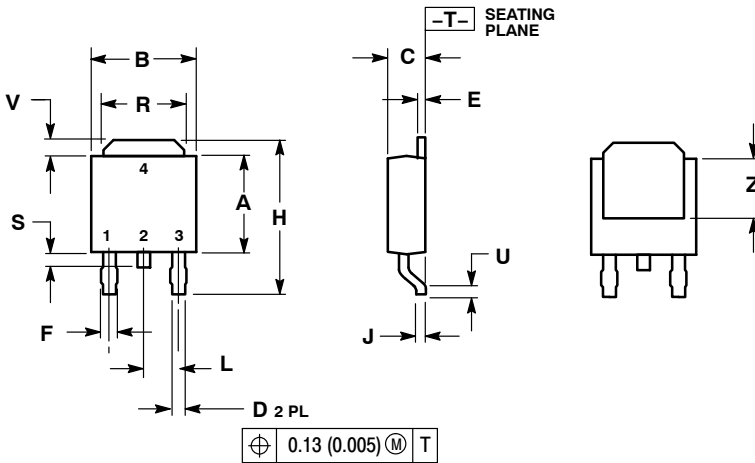
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NDF04N60Z, NDP04N60Z, NDD04N60Z

PACKAGE DIMENSIONS

DPAK
CASE 369AA-01
ISSUE A

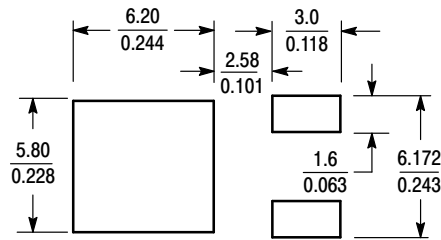


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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